

MPS-U05 (SILICON)

MPS-U06

NPN SILICON ANNULAR AMPLIFIER TRANSISTORS

... designed for general-purpose, high-voltage amplifier and driver applications.

- High Collector-Emitter Breakdown Voltage –
BV_{CEO} = 60 Vdc (Min) @ I_C = 1.0 mA_{dc} – MPS-U05
80 Vdc (Min) @ I_C = 1.0 mA_{dc} – MPS-U06
- High Power Dissipation – P_D = 10 W @ T_C = 25°C
- Complements to PNP MPS-U55 and MPS-U56

NPN SILICON AMPLIFIER TRANS



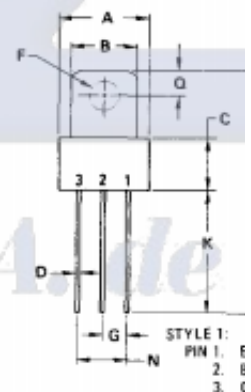
MAXIMUM RATINGS

Rating	Symbol	MPS-U05	MPS-U06	Unit
Collector-Emitter Voltage	V _{CEO}	60	80	Vdc
Collector-Base Voltage	V _{CB}	60	80	Vdc
Emitter-Base Voltage	V _{EB}	4.0		Vdc
Collector Current – Continuous	I _C	2.0		A _{dc}
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	1.0 8.0		Watt mW/°C
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	10 80		Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R _{θJC}	12.5	°C/W
Thermal Resistance, Junction to Ambient	R _{θJA} (1)	125	°C/W

(1) R_{θJA} is measured with the device soldered into a typical printed circuit board.



DIM	MILLIMETERS		MI
	MIN	MAX	
A	9.14	9.53	0.3
B	6.60	7.24	0.2
C	5.41	5.68	0.2
D	0.38	0.53	0.0
F	3.15	3.33	0.1
G	2.54 BSC		0
H	3.94	4.19	0.1
J	0.36	0.41	0.0
K	12.07	12.70	0.4
L	25.02	25.53	0.9
N	5.08 BSC		0
Q	2.39	2.69	0.0
R	1.14	1.40	0.0

CASE 152-C